AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device comprising a substrate, an n-type semiconductor layer, a light-emitting layer, and a p-type semiconductor layer, a negative electrode provided on said n-type semiconductor layer, and a positive electrode provided on said p-type semiconductor layer, the layers being successively provided atop said substrate in this order and being composed of a gallium nitride compound semiconductor, wherein said positive electrode has a three-layer structure comprising an ohmic electrode layer composed of rhodium which is in contact with said p-type semiconductor layer, an adhesion layer composed of titanium which is provided on said ohmic electrode layer and has a thickness of 10 Å or more, and a bonding pad layer provided on said adhesion layer and being composed of a metal selected from the group consisting of gold, aluminum, nickel, and copper, or composed of an alloy containing at least one of these metals.

2. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1, wherein said adhesion layer has a thickness of 500 Å to 3,000 Å.

3. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 2, wherein said adhesion layer has a thickness of 1,000 Å or more.

4. (currently amended): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1~~any one of claims 1 to 3~~, wherein said ohmic electrode layer has a thickness of 100 Å to 3,000 Å.

5. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 4, wherein said ohmic electrode layer has a thickness of 500 Å to 2,000 Å.

6. (currently amended): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1~~any one of claims 1 to 5~~, wherein said bonding pad layer has a thickness of at least 1,000 Å.

7. (original): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 6, wherein said bonding pad layer has a thickness of 3,000 Å to 5,000 Å.

8. (currently amended): A flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1~~any one of claims 1 to 7~~, wherein said bonding pad layer is composed of gold.

9. (original): A positive electrode for use in a gallium nitride compound semiconductor light-emitting device, wherein said positive electrode has a three-layer structure comprising an ohmic electrode layer composed of rhodium which is brought into contact with a p-type semiconductor layer of said compound semiconductor light-emitting device, an adhesion layer composed of titanium which is provided on said ohmic electrode layer and has a thickness of 10 Å or more, and a bonding pad layer provided on said adhesion layer, said bonding pad layer being composed of a metal selected from the group consisting of gold, aluminum, nickel, and copper, or composed of an alloy containing at least one of these metals.

10. (original): A positive electrode for use in gallium nitride compound semiconductor light-emitting device according to claim 9, wherein said adhesion layer has a thickness of 500 Å to 3,000 Å.

11. (currently amended): A positive electrode for use in a gallium nitride compound semiconductor light-emitting device according to claim 9 ~~or 10~~, wherein said adhesion layer has a thickness of 1,000 Å or more.

12. (currently amended): A light-emitting diode comprising a flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1 ~~any one of claims 1 to 8~~.

13. (currently amended): A lamp comprising a flip-chip-type gallium nitride compound semiconductor light-emitting device according to claim 1~~any one of claims 1 to 8~~.